

Innovative Mask Aligner Lithography for MEMS and Packaging



Dr. Reinhard Voelkel

CEO SUSS MicroOptics SA

September 9th, 2010



國際半導體設備材料產業協會

Micro-Optics in Front-End Lithography

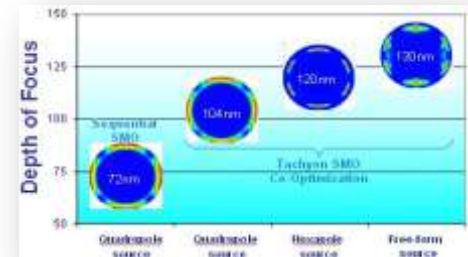


Customized Illumination
Pupil Shaping (DOE)
Now: FlexRay™
programmable illumination
technology

Excimer Laser (193nm)
Laser Beam Shaping
Laser Beam Homogenizing



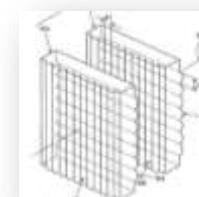
Micro-Optics is Key Enabling Technology in
Front-End Lithography



Customized Illumination



Diffractive Optical Elements (DOE)
MEMS (FlexRay™)



Microlens
Homogenizer



MEMS: Photolithography

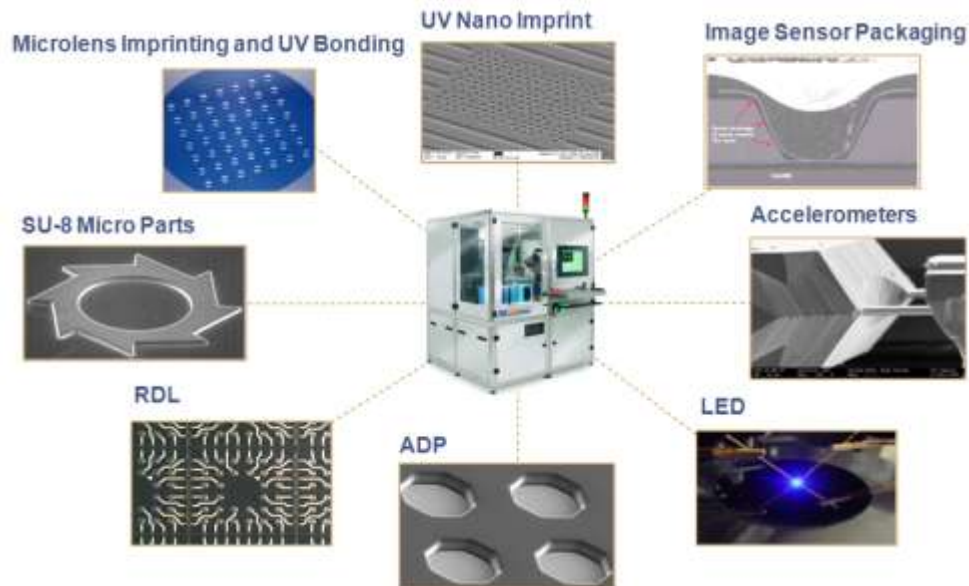
Mask Aligners are the work horse of SEMI industry since the very beginning



SÜSS MicroTec MA200 Compact

Photolithography

Mask Aligners are used for MEMS, Packaging and SEMI



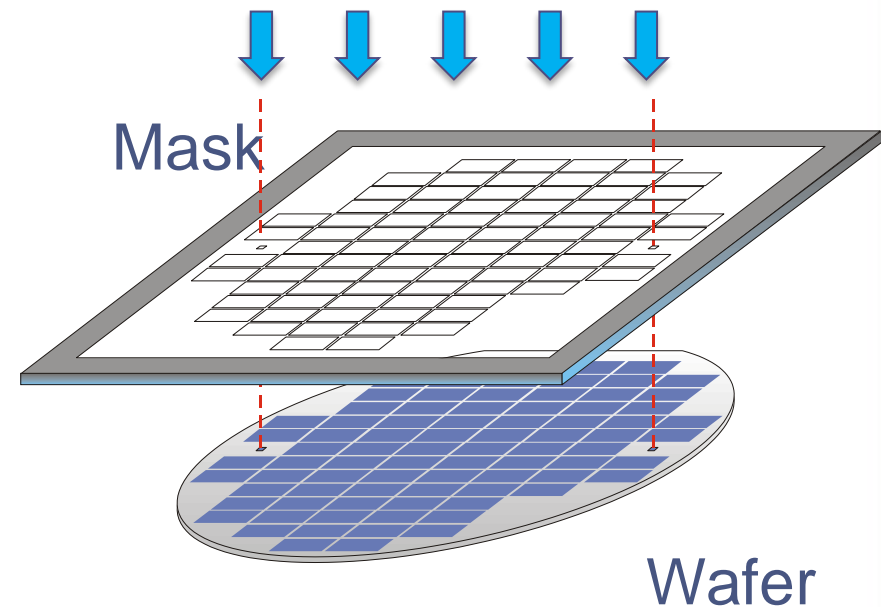
SUSS MicroTec MA200 Compact

Back End Lithography

Mask Aligners Lithography is „Shadow Printing“

Mask illumination using UV light

Resolution \Leftrightarrow proximity gap



Photolithography

Mask Aligners are

- Mature technology
- Cost-effective
- Fast (high throughput)
- Service friendly
- Easy to use
- Convenient



SUSS MicroTec MA200 Compact

Challenge

BUT

a Mask Aligner is
a Mask Aligner is
a Mask Aligner!

Myth or Facts?

Reaching limits: Change to Projection?

Think twice, because

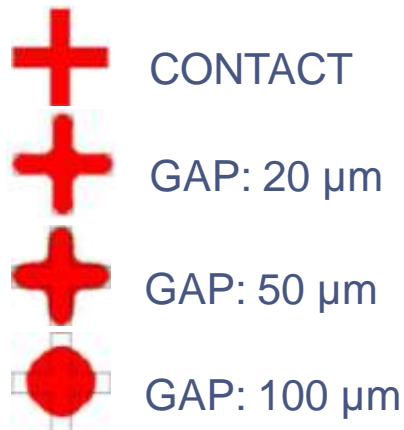
- High capital investment
- High costs per wafer
- Change established processes
- Reduced focus budget
- Can't print to the very edge of wafer...

Mask Aligners are so convenient!

Mask Aligner Lithography

illumination makes the difference!

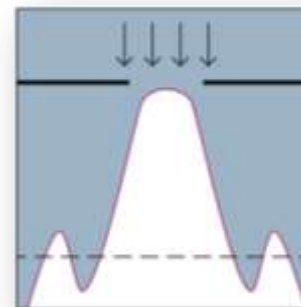
- Diffraction
- Partial Coherence



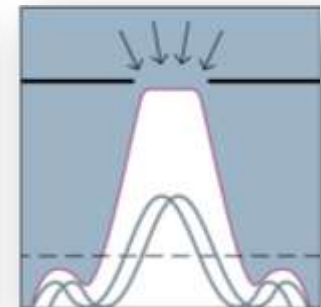
Parallel Light



Diffuse Light

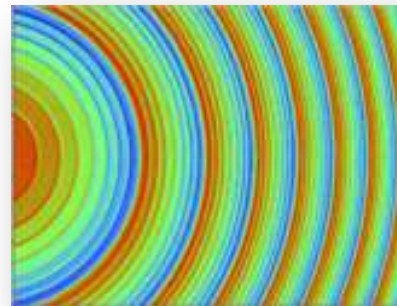
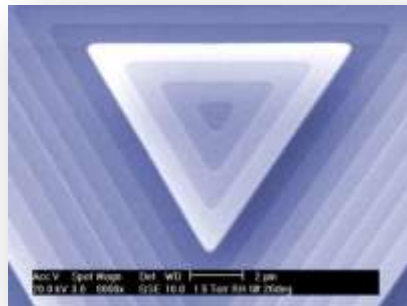
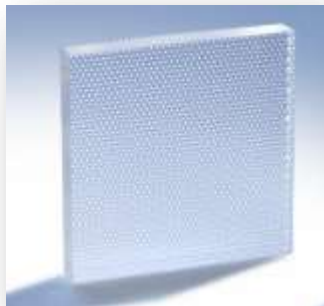


Parallel Light

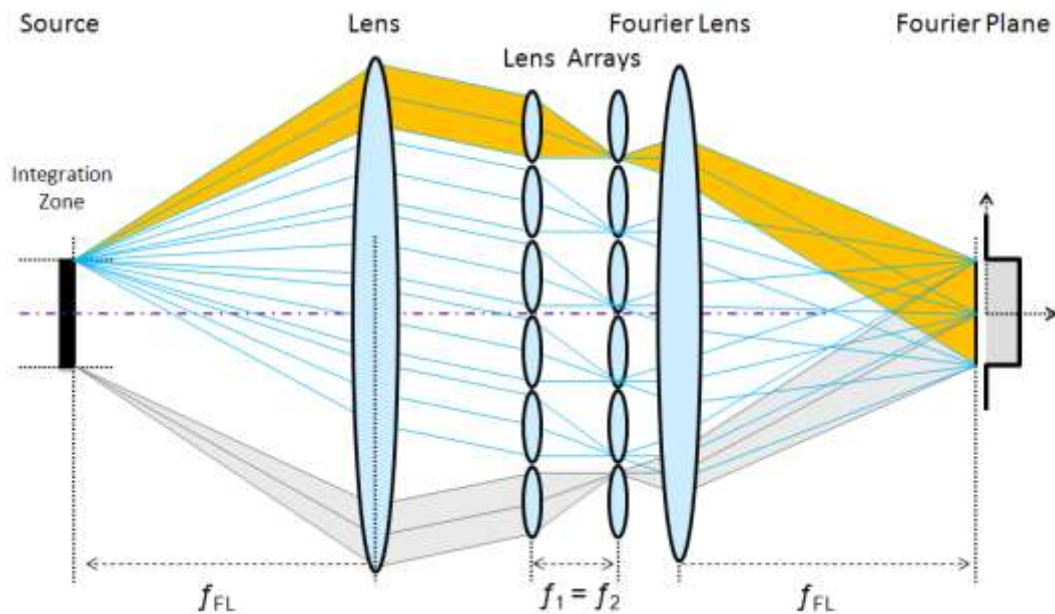


Apodization

Micro-Optics is also Key Enabling Technology for Mask Aligners!

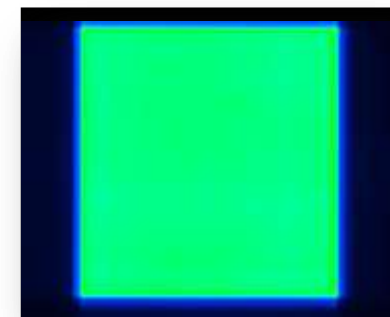
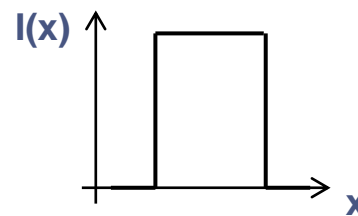
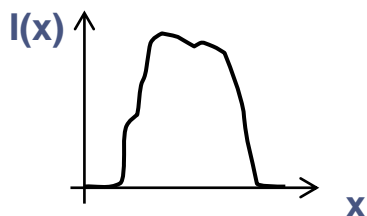


Fly's Eye Homogenizer Microlens Optical Integrator (Köhler)



August Köhler
(1866-1948)

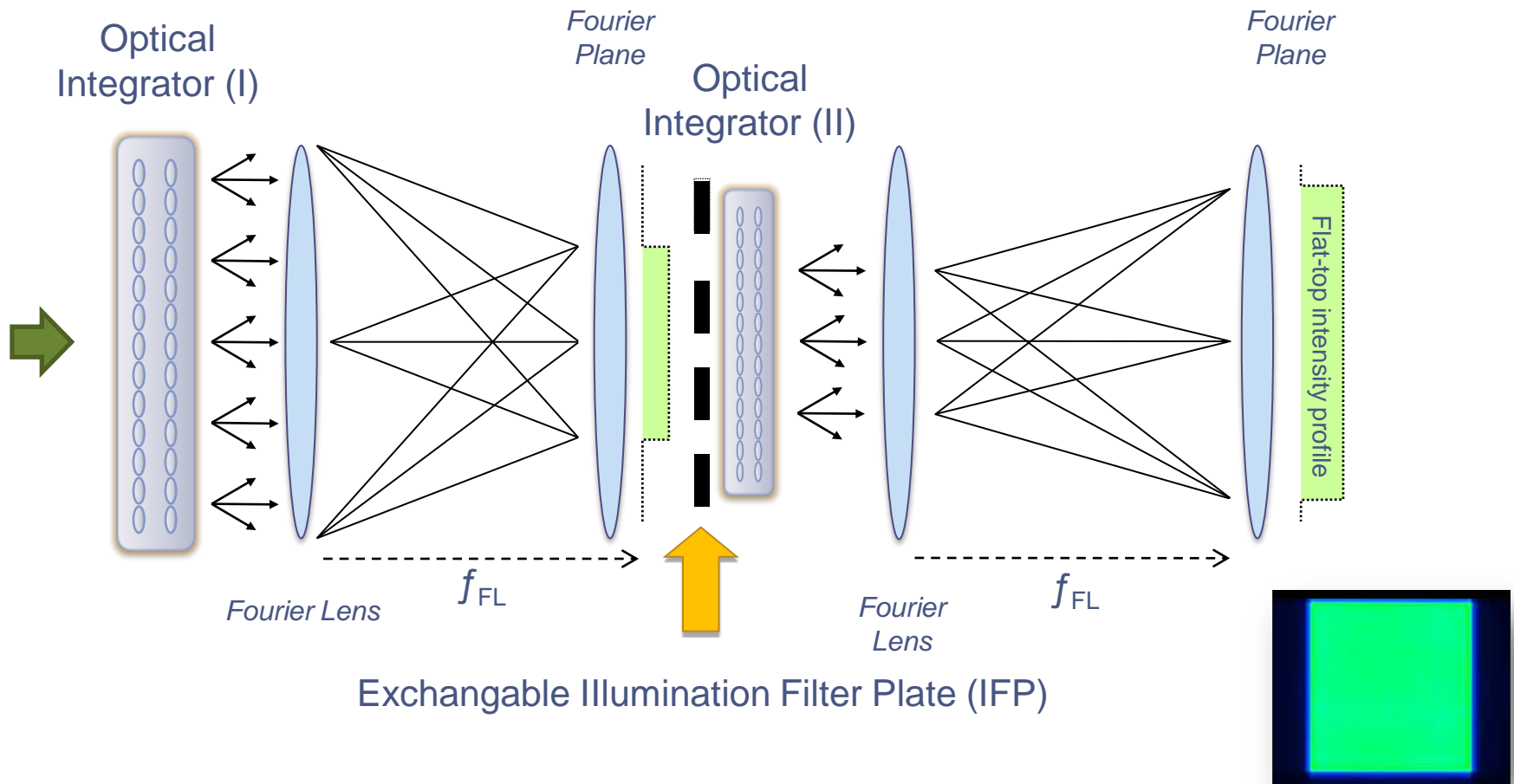
Flat-Top Intensity Profile



MO EXPOSURE OPTICS

Innovative Illumination System for SUSS Mask Aligners

Technology Backbone: Microlens Optical Integrators (Köhler)

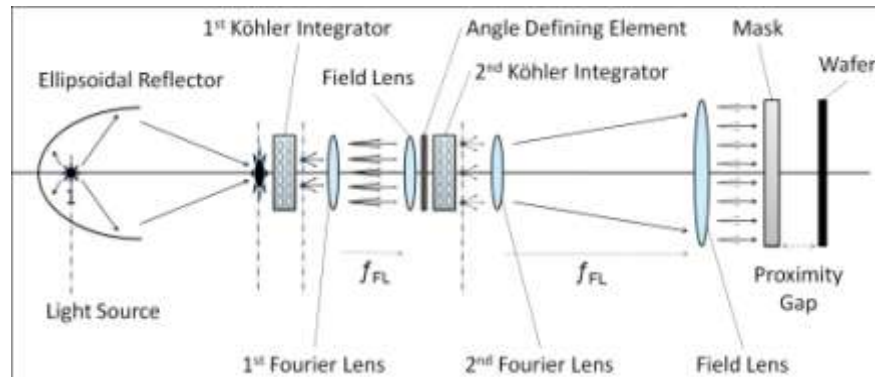


Patent pending

MO Exposure Optics



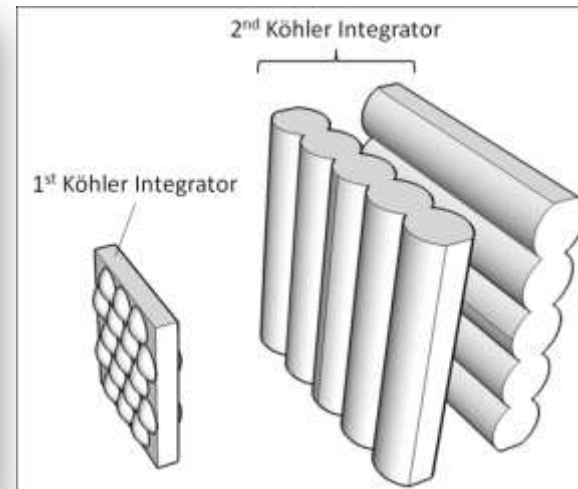
Library of Illumination Filter Plates (IFP)



Microlens Array

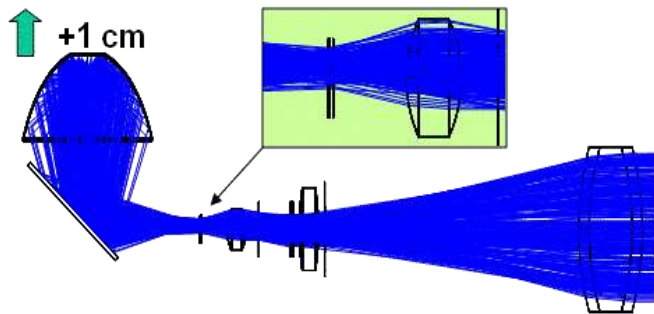


Optical System MA 200

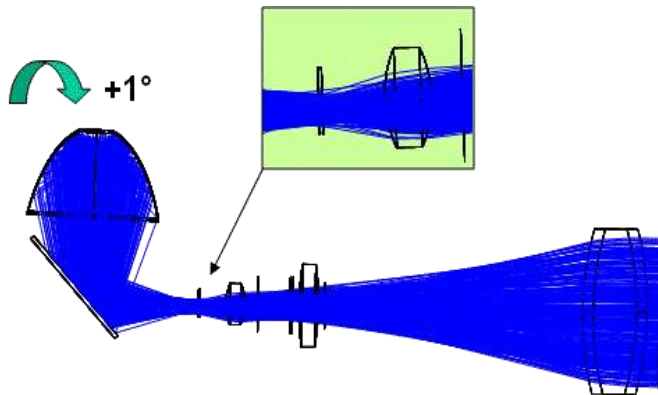


Microlens-based Optical Integrators

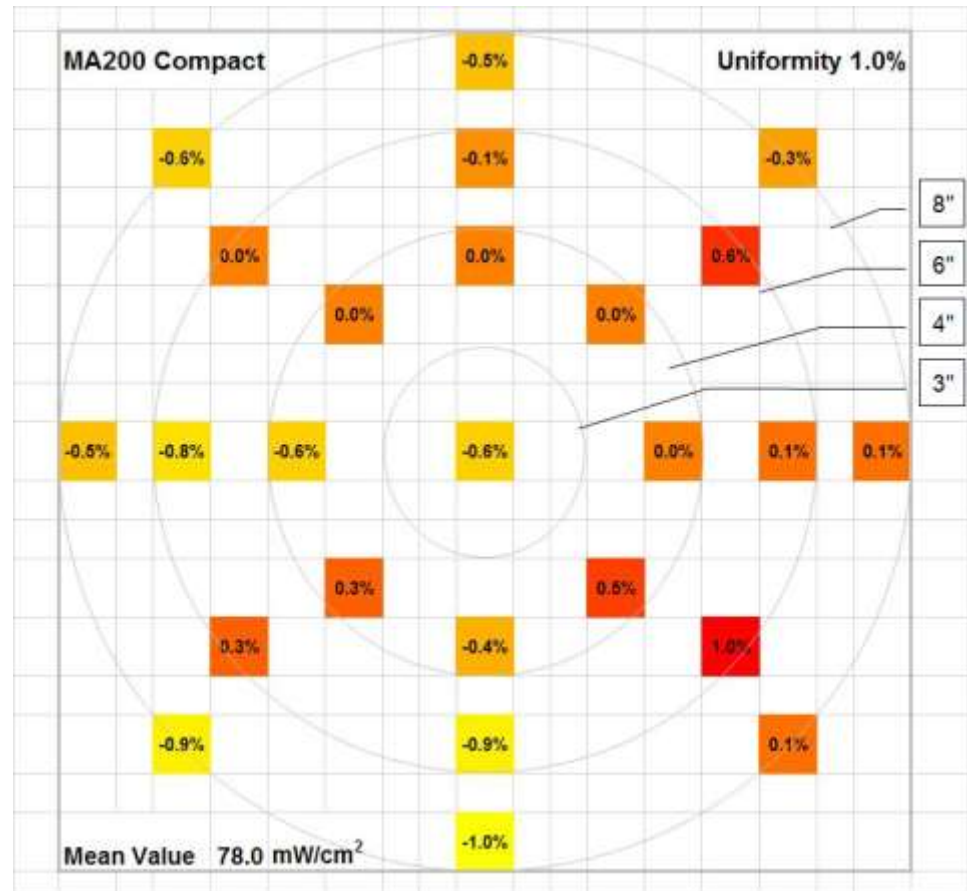
Excellent Uniformity Independent of Lamp Position



Lamp Position: Uncritical



Lamp Tilt: Uncritical

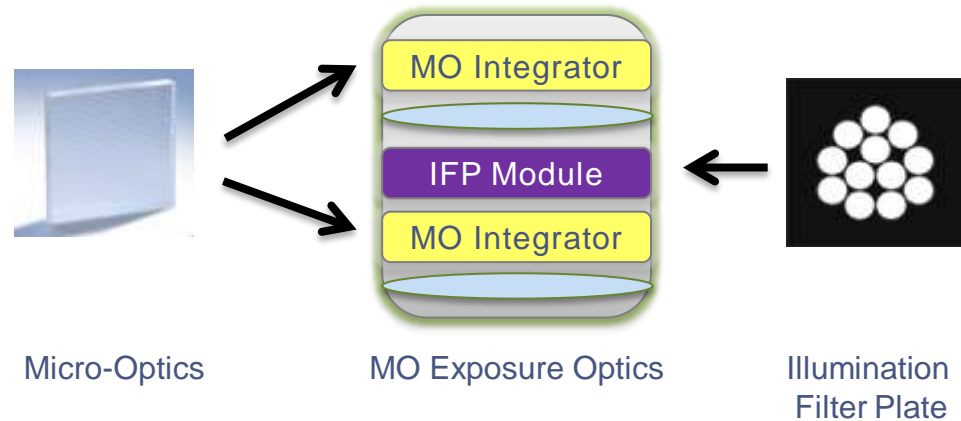


Deviation from mean value in [%] for Ø200mm in MA200 Compact

Stabilize the Mask Aligner

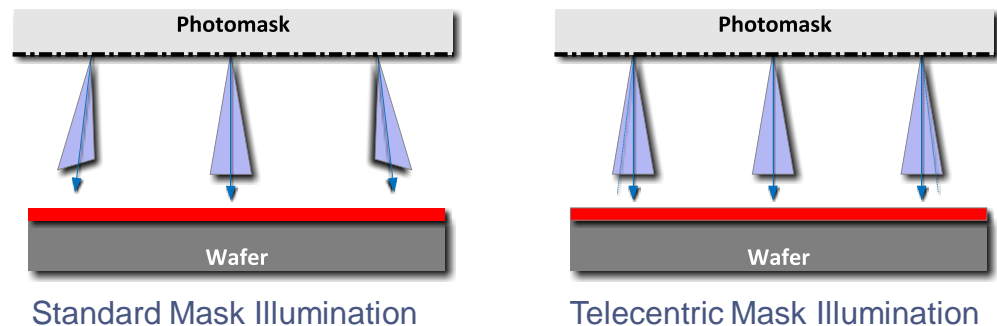
Features

- Stable Light Source
- Excellent Uniformity
- Telecentric Illumination



Benefits

- Reduced Downtime
- Improved CD Uniformity
- Larger Process Window
- Higher Yield



Technology Enhancement

Microlens-based MO Exposure Optics provides

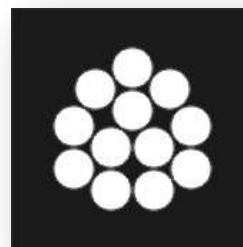
- Stabilized light source
- Excellent light uniformity
- Telecentric illumination

in Mask Aligners

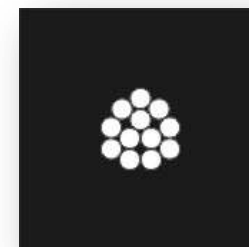
Exchangeable Illumination Filter Plates

Features

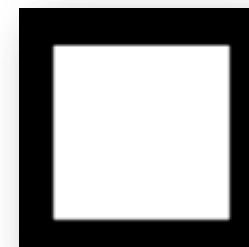
- HR to LGO change in less than 1 min
- Illumination filter plates (IFP)
- Customized illumination



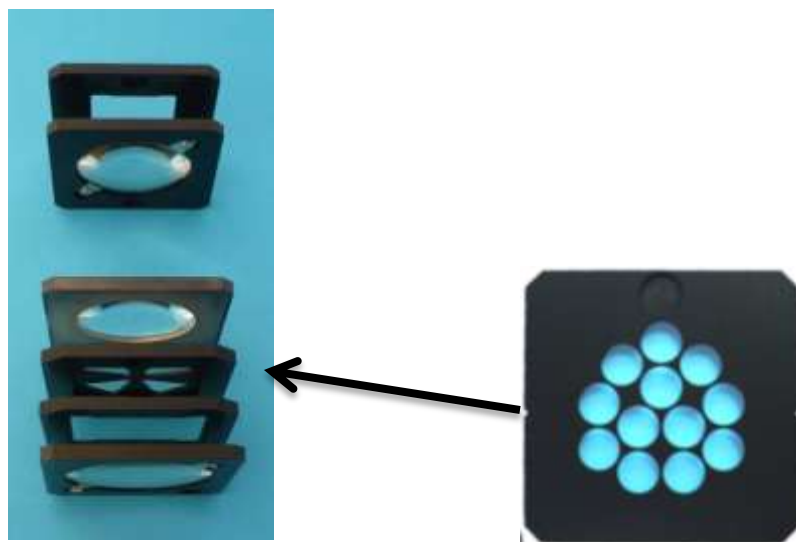
IFP-HR
„High Resolution“



IFP-LGO
„Large Gap“

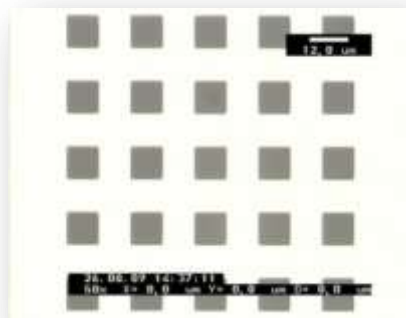


IFP-C90
„More Light“

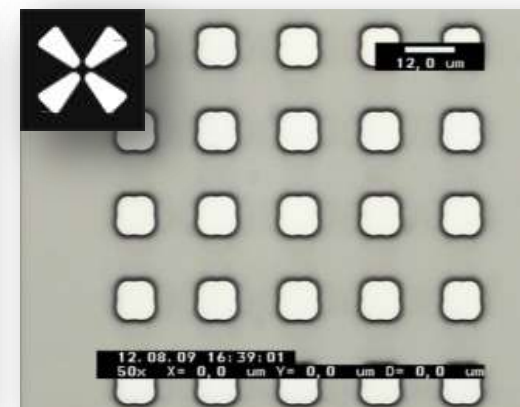
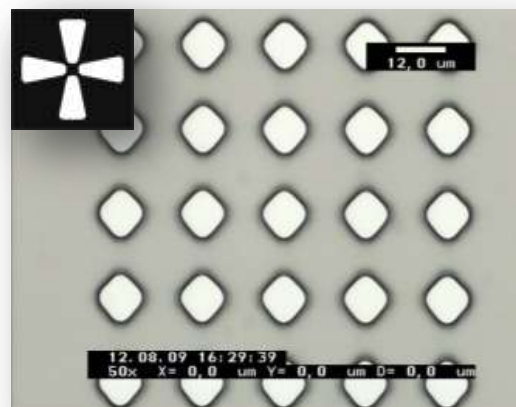
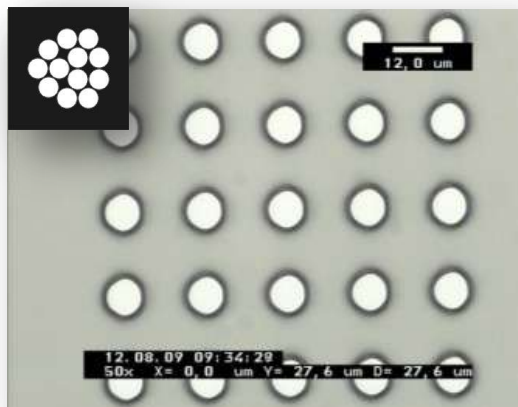


Exchangeable Illumination Filter Plate (IFP)

Optimize Diffraction Customized Illumination



Photomask Pattern
Square $10 \times 10 \mu\text{m}^2$

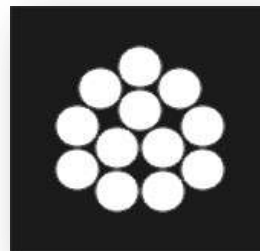


1.2 μm thick resist (AZ 4110), 100 μm Proximity Gap, SUSS MA8

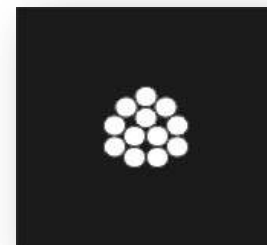
Optimize Diffraction Customized Illumination

Features

- HR to LGO change in <1 min
- Illumination filter plates (IFP)
- Customized illumination



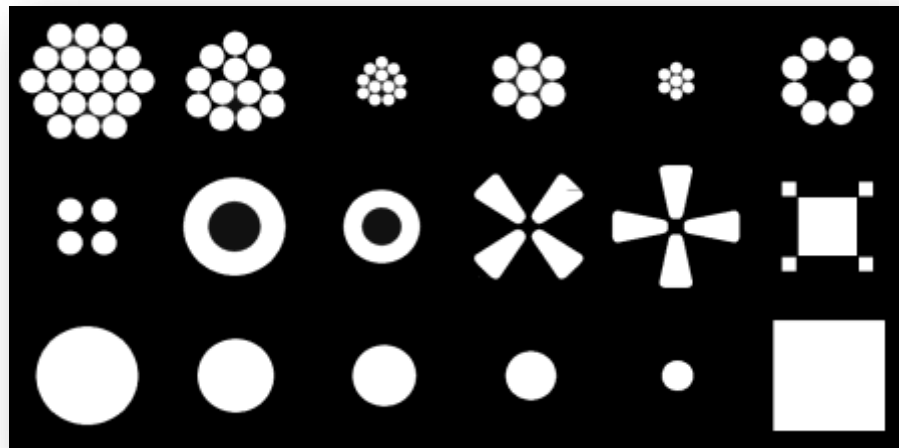
HR: High Resolution



LGO: Large Gap

Benefits

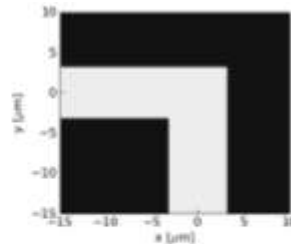
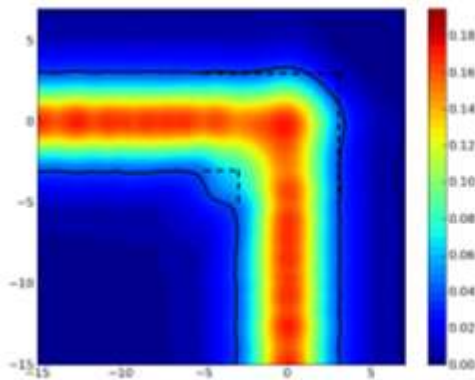
- Flexible illumination
- Diffraction reduction
- Resolution enhancement technology (RET)
- Optimized lithography process



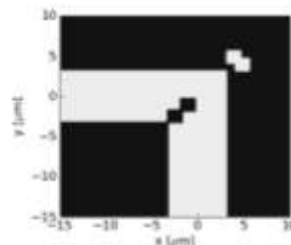
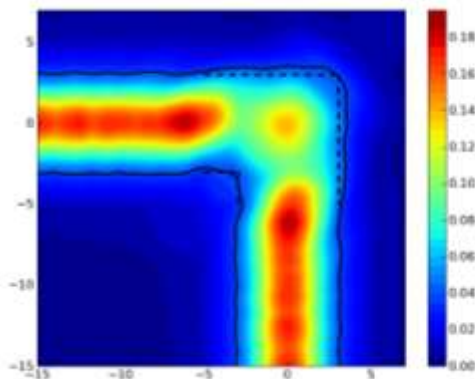
Library of Illumination Filter Plates (IFP)

Optical Proximity Correction (OPC)

Aerial image (simulation)



Mask pattern

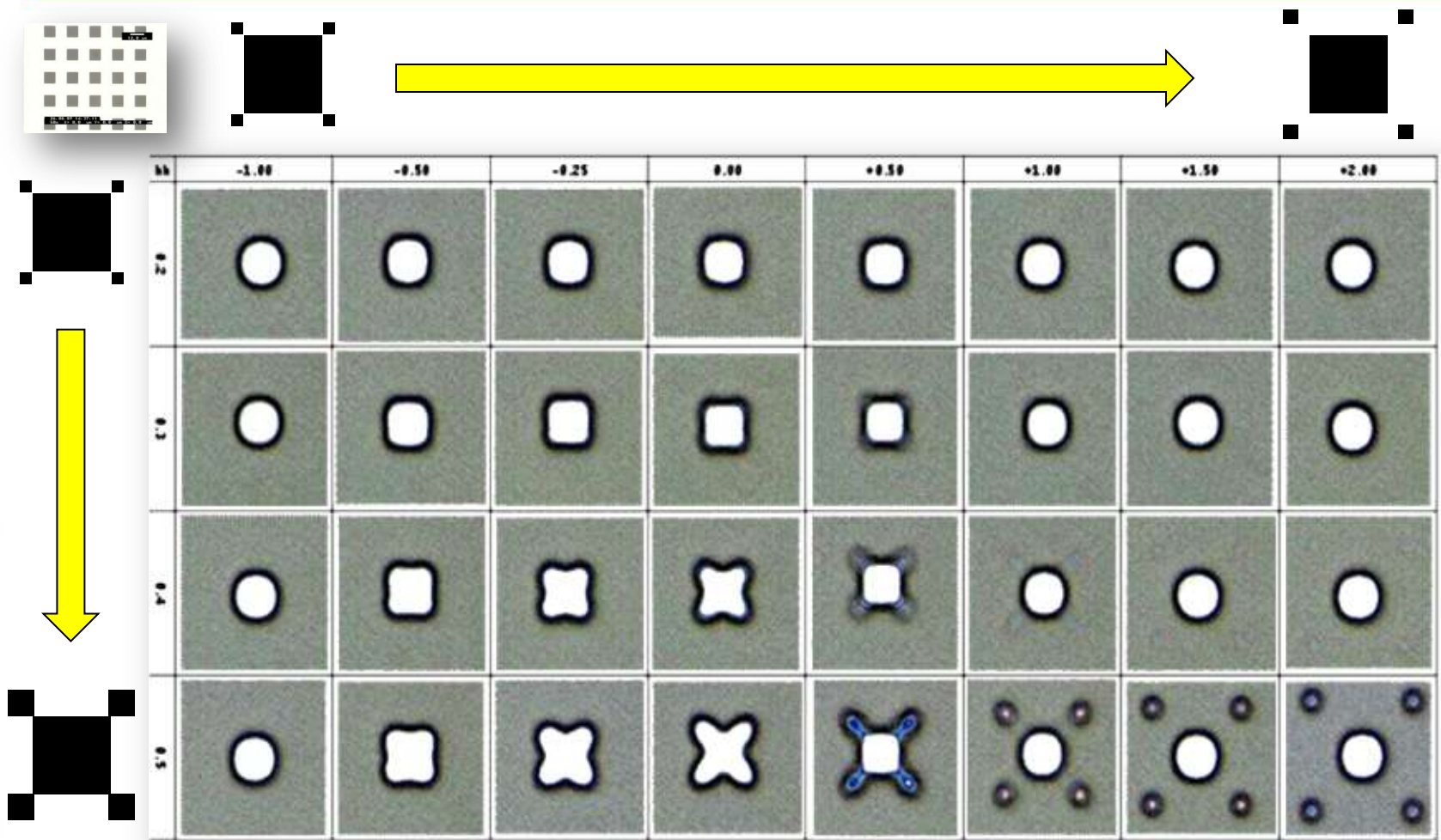


OPC assist features

Aerial image 6µm line
 Proximity gap 40µm
 Mask layouts (right)
 OPC assist features (bottom)
 Reduction of the rounding of
 the inner and outer corner

Ref: Kristian Motzek, FhG-IISB, SUSS Report Sept 2010

Optical Proximity Correction (OPC)



Square 10 μ m x 10 μ m, Proximity Gap 50 μ m, Photoresist AZ4110, 1.2 μ m thick

Expertise in Lithography Simulation

Lithography Simulation
Source-Mask Optimization Service
Research & Technology Partners

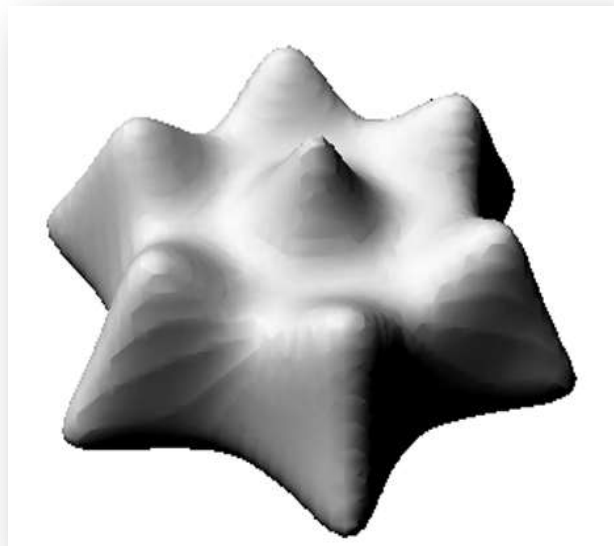
TOPPAN
TOPPAN PHOTOMASKS, INC.

Fraunhofer
IISB

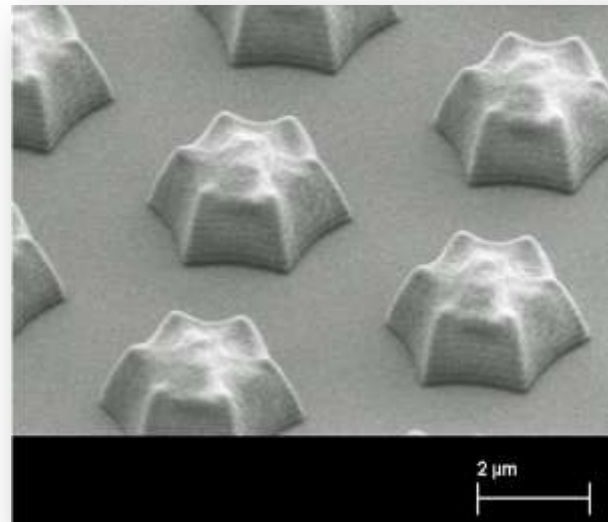
Fraunhofer
IOF

FHV
University of Applied Sciences

GenISys

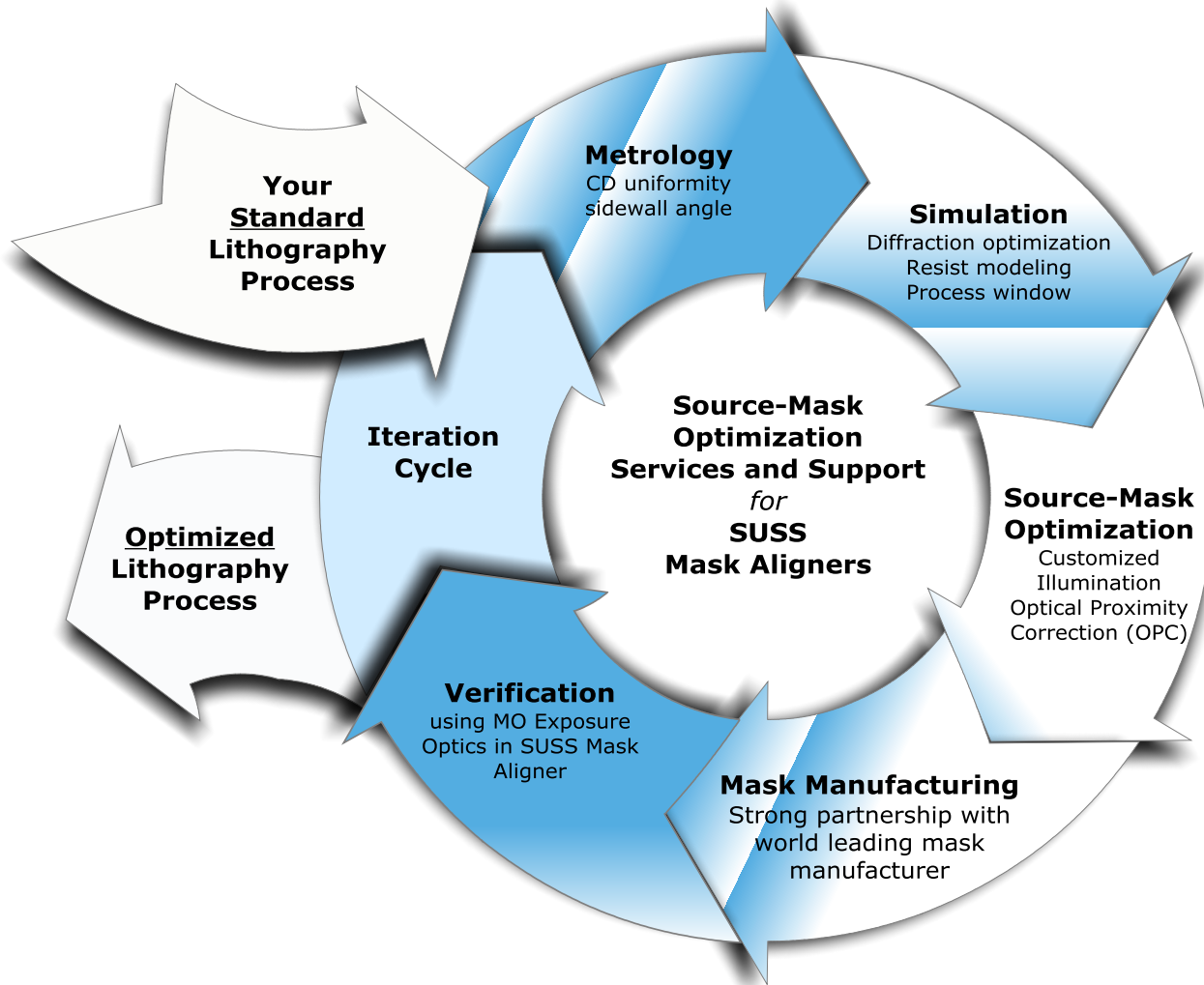


Simulation 3D Resist Structure
(Layout Lab, GenISys)



Printed Resist Structure

Source-Mask Optimization Service



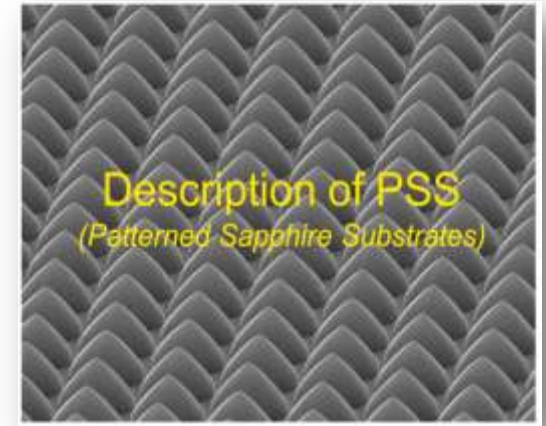
Example: LED Requirements for PSS

Patterned Sapphire Substrate

- Epitaxy
- Efficiency
- Beam Confinement

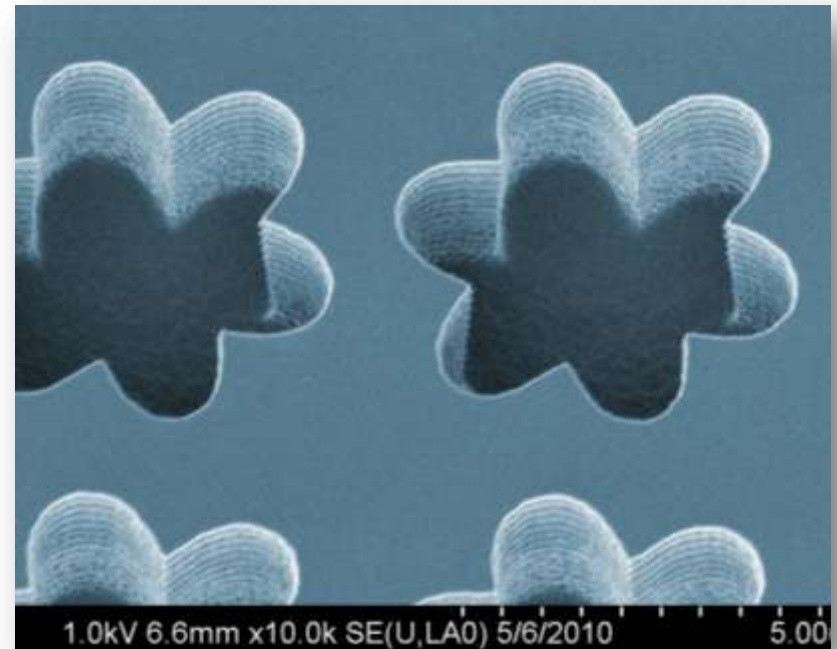
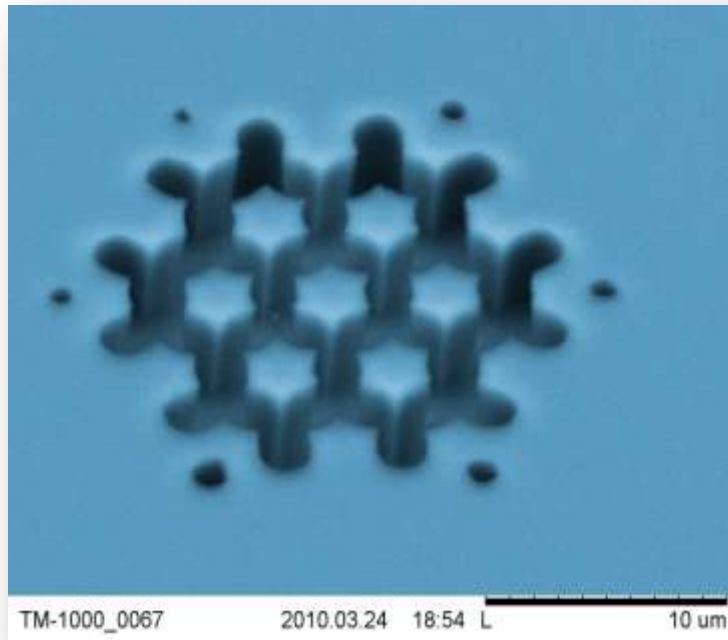
Process

- Hexagons/Cones, $\approx 3\mu\text{m}$
- RIE-ICP (Chlorine) Etching



www.corial.net

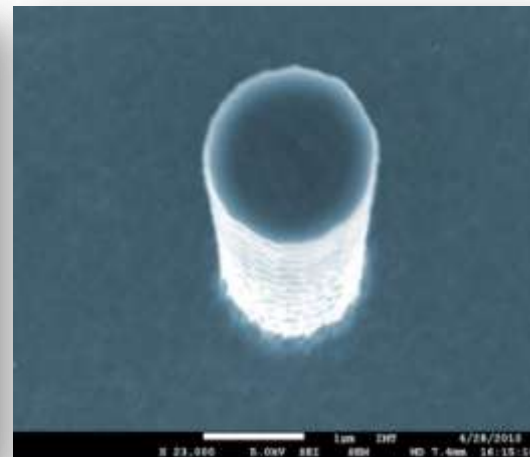
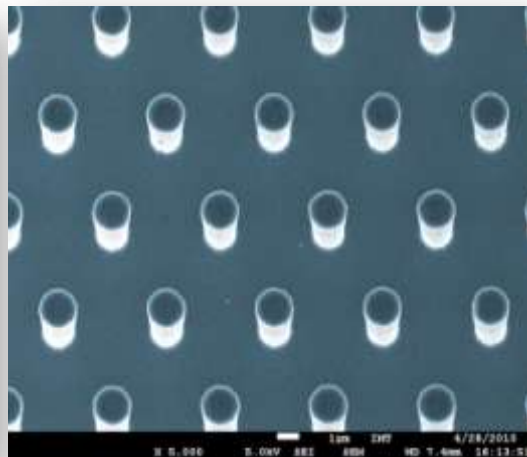
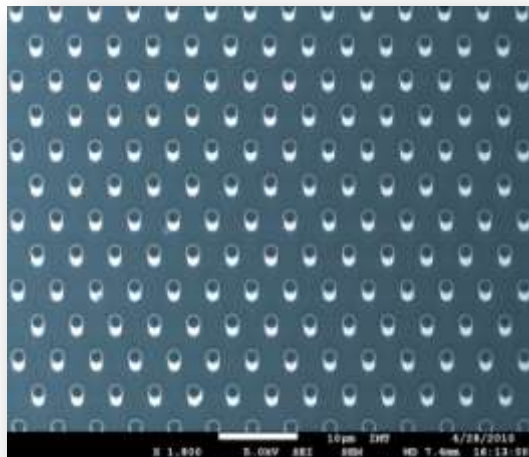
Example: LED Source-Mask Optimization



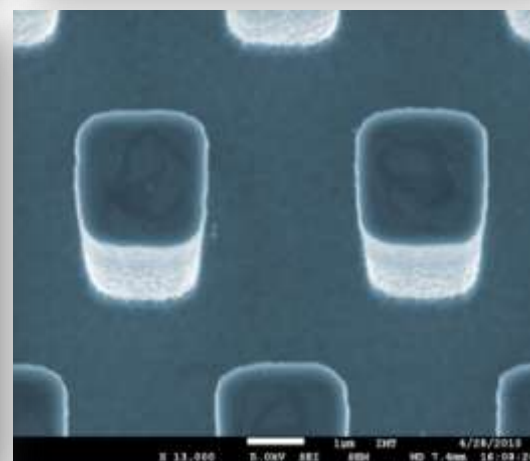
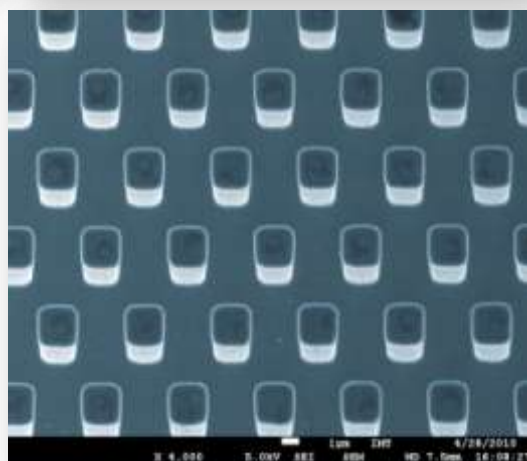
Optical Proximity Correction
(Proximity Gap 30 μ m)

MO Talbot Lithography
(Proximity Gap 102 μ m)

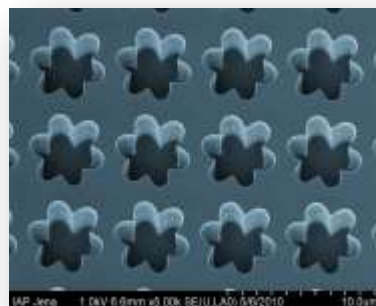
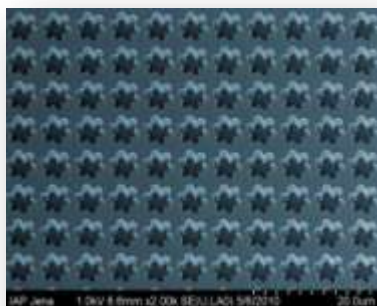
MO Talbot Lithography Periodic Structures (PSS)



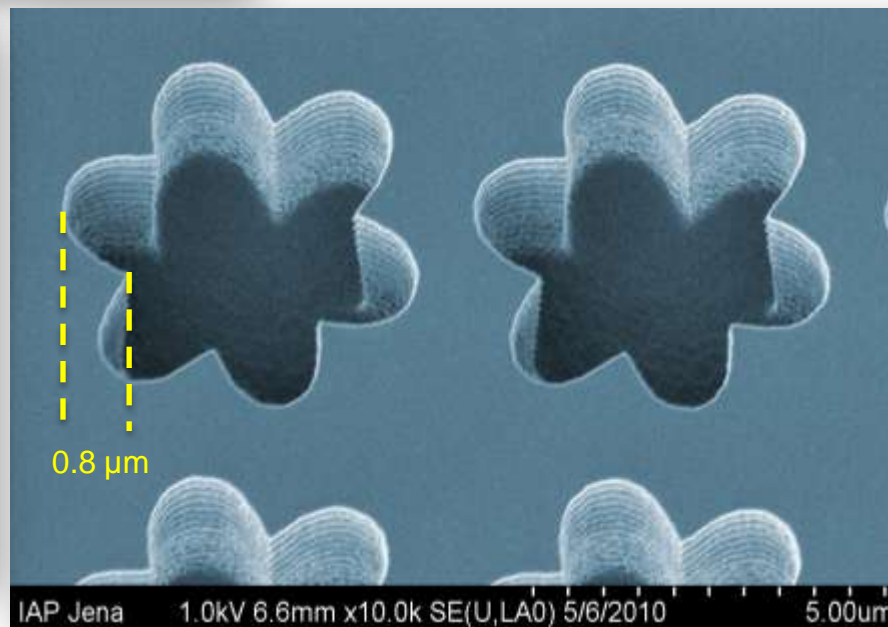
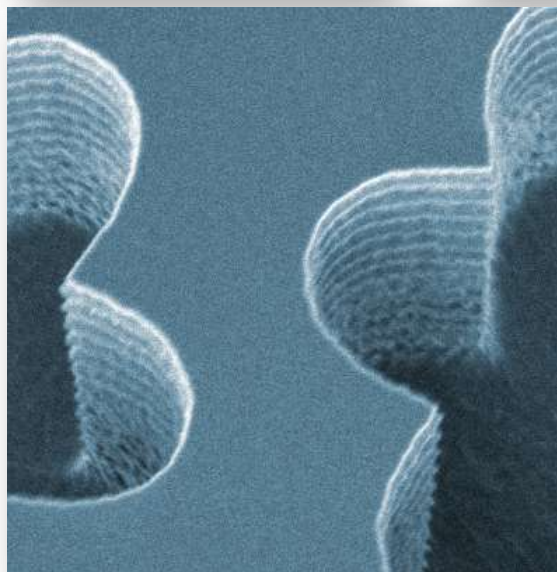
<i>Pitch</i>	<i>5 μm</i>
<i>Resist</i>	<i>2 μm thick</i>
<i>Etching</i>	<i>RIE (Bosch)</i>
	<i>Silicon</i>
<i>Proximity Gap</i>	<i>102 μm</i>



MO Talbot Lithography Periodic Structures (PSS)



<i>Pitch</i>	5 μm
<i>Resist</i>	2 μm thick
<i>Etching</i>	RIE (Bosch) Silicon
<i>Proximity Gap</i>	102 μm

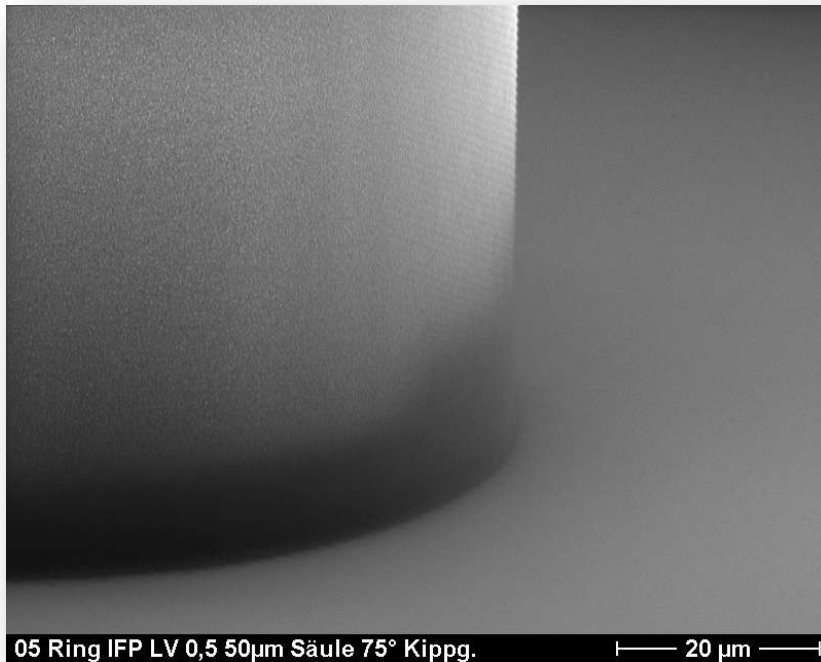


MEMS

Thick Photoresist (SU8)

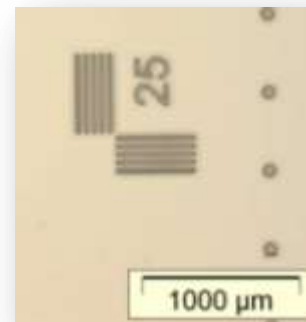
Very thick photoresist

- Improvement of Footing
- Sidewall shaping



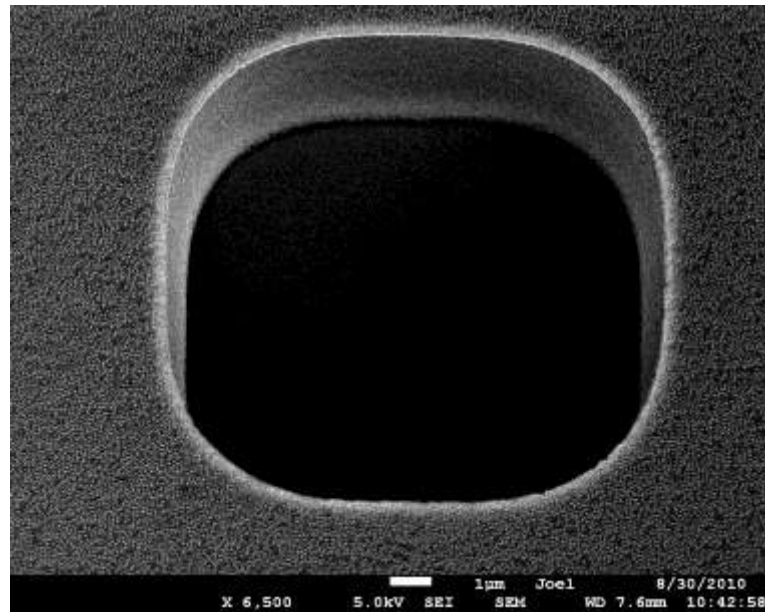
Improvement of footing and sidewalls with thick SU8 using MO Exposure Optics

300µm thick SU8
Resolution 25µm



micro resist
technology

Example: ADP, TSV & 3D OPC Fresnel

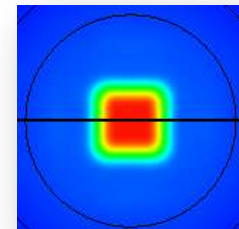
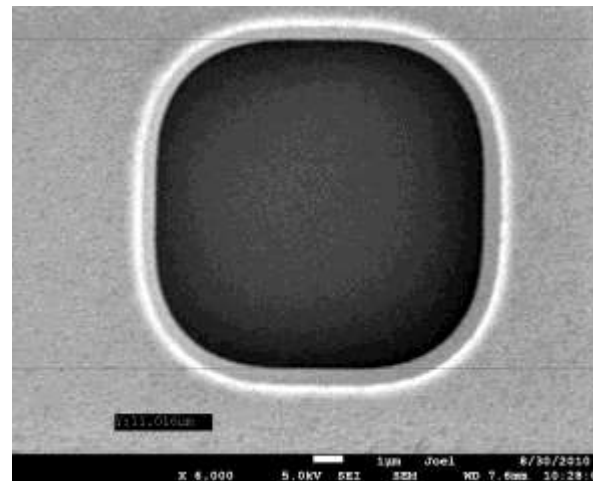


Side view

Photoresist AZ1518, 5µm thick

11µm via
800µm proximity gap

Top view

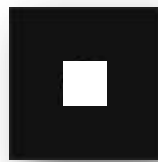
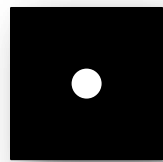


Via shaping

SUSS MicroOptics

TOPPAN
TOPPAN PHOTOMASKS, INC.

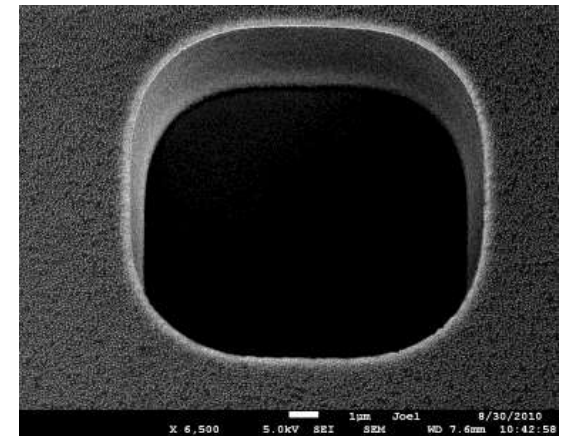
Example: ADP, TSV & 3D OPC Fresnel



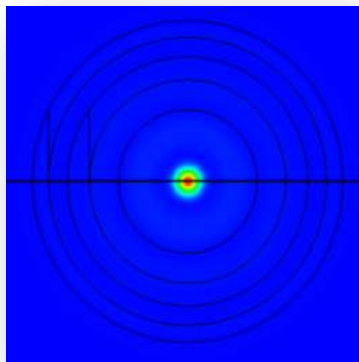
Illumination Filter Plates (IFP)



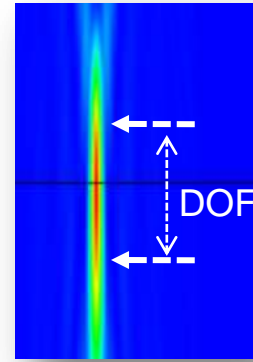
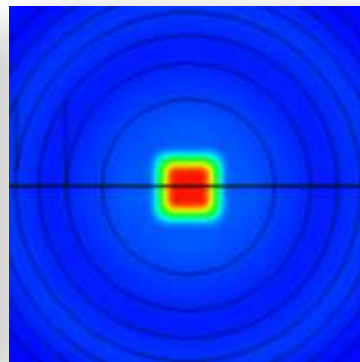
OPC Structure (Fresnel-type)



11µm via at 800 µm proximity gap



Resulting Aerial Image



Depth of focus (DOF)

Example: ADP, TSV & 3D OPC Fresnel

Benefits

- Very large proximity gap
- Via shaping possible
- Extended Depth of Focus (DOF)
- Very short exposure time (throughput)

Typical parameters for via printing
using OPC Fresnel Technology

Gap	Ø _{Via}	DOF
100 µm	2 µm	5 µm
200 µm	3 µm	15 µm
300 µm	5 µm	30 µm
400 µm	7 µm	60 µm
500 µm	10 µm	100 µm
700 µm	14 µm	200 µm

MO Exposure Optics Available for all SUSS Mask Aligners



MA6, MA8



MJB4



LithoPack 300



MA/BA8 Gen3



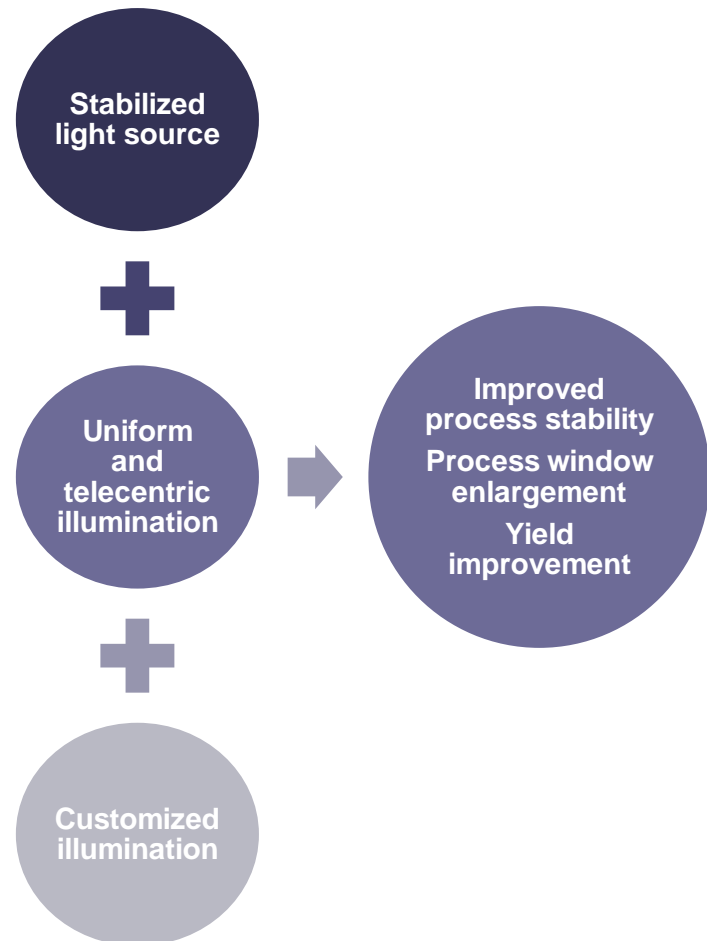
MA200Compact,
MA100e, MA150e



MA300 Gen2

Advanced Mask Aligner Lithography

A Mask Aligner is a
Mask Aligner is a
Mask Aligner!
Yes! But...



Technology Enhancement

MO Exposure Optics enables

- Customized Illumination
- Optical Proximity Correction (OPC)
- Source-Mask Optimization (SMO)

in SUSS Mask Aligners

Advanced Mask Aligner Lithography

Summary

Quick wins

- Improved CD uniformity
- Higher throughput
- Less downtime

New process parameter: Illumination!

- Customized illumination
- Optical Proximity Correction (OPC)

SUSS.

Our Solutions Set Standards

SUSS MicroTec
SUSS MicroOptics

www.suss.com

